

isc Silicon NPN Power Transistor

3DD207i

DESCRIPTION

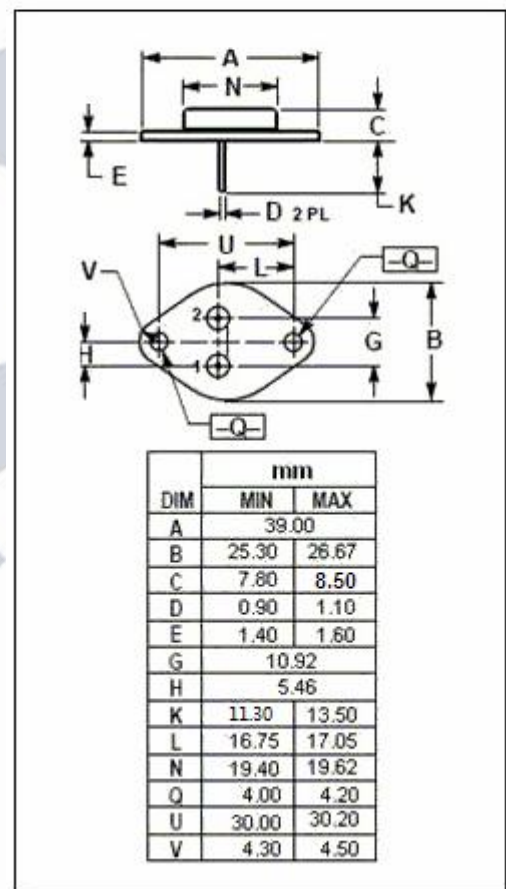
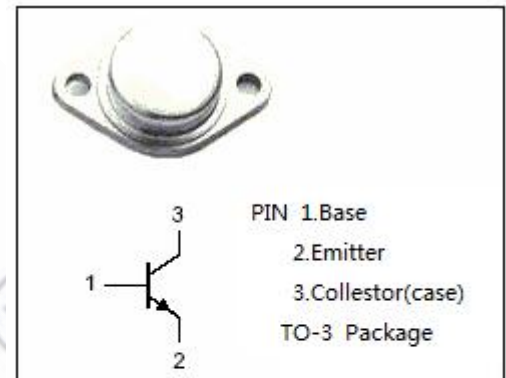
- Collector-Emitter Breakdown Voltage:
: $V_{(BR)CEO} = 200V(\text{Min.})$
- Collector-Emitter Saturation Voltage:
: $V_{CE(sat)} = 1.0V(\text{Max}) @ I_C = 3A$

APPLICATIONS

- Designed for auto amplifier application.

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	200	V
V_{CEO}	Collector-Emitter Voltage	200	V
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current-Continuous	5	A
P_C	Collector Power Dissipation@ $T_C=75^\circ\text{C}$	50	W
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature	-55~150	$^\circ\text{C}$



isc Silicon NPN Power Transistors**3DD207i****ELECTRICAL CHARACTERISTICS** $T_C=25^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C=50\text{mA}; I_B=0$	200		V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	$I_C=1\text{mA}; I_E=0$	200		V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E=1\text{mA}; I_C=0$	6		V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=3\text{A}; I_B=0.3\text{A}$		1.0	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C=3\text{A}; I_B=0.3\text{A}$		1.5	V
I_{CBO}	Collector Cutoff Current	$V_{CB}=200\text{V}; I_E=0$		0.5	mA
h_{FE}	DC Current Gain	$I_C=1\text{A}; V_{CE}=4\text{V}$	100	200	